

TO-92 Plastic-Encapsulate Transistors

2SA719/2SA720 TRANSISTOR (PNP)

FEATURES

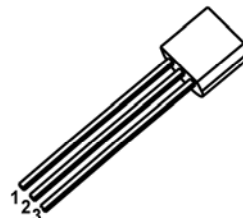
- For Low-Frequency Power Amplification and Driver Amplification

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage 2SA719	-30	V
	2SA720	-60	
V _{CEO}	Collector-Emitter Voltage 2SA719	-25	V
	2SA720	-50	
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-500	mA
P _C	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-92

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



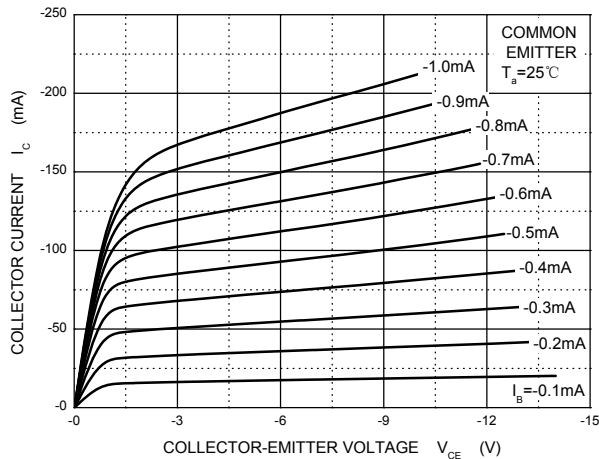
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10uA, I _E =0	-30			V
			-60			
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-25			V
			-50			
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10uA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -20V, I _E =0			-0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0			-0.1	uA
DC current gain	h _{FE(1)}	V _{CE} =-10V, I _C = -150mA	85		340	
	h _{FE(2)}	V _{CE} =-10V, I _C = -500mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-300mA, I _B = -30mA			-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -300mA, I _B =-30mA			-1.5	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -50mA f = 200MHz		200		MHz
Collector Output Capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			15	pF

CLASSIFICATION h_{FE(1)}

Rank	Q	R	S
Range	85-170	120-240	170-340

Static Characteristic



h_{FE} — I_c

